Top View

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Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

PowerPAK® 1212-8SH D D D D 8 5 D 7 8 4 3 2 S 8 S S

PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.00215			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00310			
Q _g typ. (nC)	22.5			
I _D (A)	40 g			
Configuration	Sinale			

Bottom View

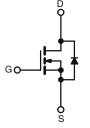
FEATURES

- TrenchFET® Gen IV power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

- Switch mode power supplies
- · Personal computers and servers
- · Telecom bricks
- VRM's and POL



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8SH
Lead (Pb)-free and halogen-free	SiSHA04DN-T1-GE3

ABSOLUTE MAXIMUM RATING	iS (T _A = 25 °C, u	nless otherv	vise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	30	V
Gate-source voltage		V_{GS}	+20, -16	v
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		40 ⁹	
	T _C = 70 °C		40 ⁹	
	T _A = 25 °C	l _D	30.9 ^{a, b}	
	T _A = 70 °C		28.3 ^{a, b}	Α
Pulsed drain current (t = 300 μs)		I _{DM}	80	A
Continuous source-drain diode current	T _C = 25 °C		40 g	
	T _A = 25 °C	l _S	3.3 ^{a, b}	
Single pulse avalanche current L = 0.		I _{AS}	20	
Single pulse avalanche energy	L=0.11IIII	E _{AS}	20	mJ
	T _C = 25 °C		52	
Maximum naurar dissination	T _C = 70 °C		43	w
Maximum power dissipation	T _A = 25 °C	P _D	3.7 ^{a, b}	VV
	T _A = 70 °C		3.1 ^{a, b}	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) c, d			260	

THERMAL RESISTANCE RATI	NGS				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient a, e	t ≤ 10 s	R _{thJA}	24	33	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.9	2.4	C/VV

Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. t = 10 s
- c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- e. Maximum under steady state conditions is 81 °C/W
- f. Based on T_C = 25 °C
- g. Package limited

Document Number: 76879

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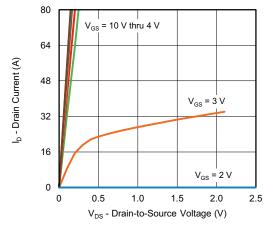
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			1	L	L	l
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	$\Delta V_{DS}/T_{J}$		14	-	1400
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$	-	-5.5	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.1	-	2.2	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 V, -16 V	-	-	±100	nA
Zero gate voltage drain current		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	Α
Drain-source on-state resistance ^a	, ,	V _{GS} = 10 V, I _D = 15 A	-	0.00180	0.00215	
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A	-	0.00250	0.00310	Ω
Forward transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A	-	105		S
Dynamic ^b		-	1	L	L	
Input capacitance	C _{iss}		-	3595	-	
Output capacitance	C _{oss}	V 45VV 6V (4 M)	-	1040	-	рF
Reverse transfer capacitance	C _{rss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	79	-	
C _{rss} /C _{iss} ratio			-	0.022	0.044	
Total gate charge	Q _g	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$	-	51	77	
			-	22.5	34	
Gate-source charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	_	8.6	-	nC
Gate-drain charge	Q _{gd}		-	4	-	
Output charge	Q _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}$	-	30.5	-	
Gate resistance	R _q	f = 1 MHz	0.3	1.25	2.5	Ω
Turn-on delay time	t _{d(on)}		-	24	48	
Rise time	t _r	$V_{DD} = 15 \text{ V}, R_1 = 1.5 \Omega$	_	17	34	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	25	50	
Fall time	t _f		-	10	20	
Turn-on delay time	t _{d(on)}		-	12	24	ns
Rise time	t _r	$V_{DD} = 15 \text{ V}, R_1 = 1.5 \Omega$	_	10	20	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	30	60	
Fall time	t _f		-	8	16	
Drain-Source Body Diode Characteristi	cs		1	L	L	
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	40	
Pulse diode forward current	I _{SM}		-	-	80	Α
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.73	1.1	V
Body diode reverse recovery time	t _{rr}	<u> </u>	-	36	70	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	_	24	48	nC
Reverse recovery fall time	t _a	$T_{\text{J}} = 25 ^{\circ}\text{C}$	-	16	-	1
Hevelse recovery fall time						

Notes

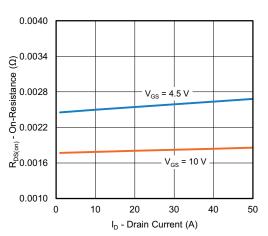
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

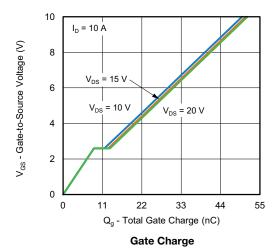


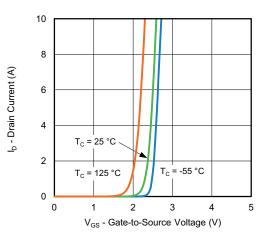


Output Characteristics

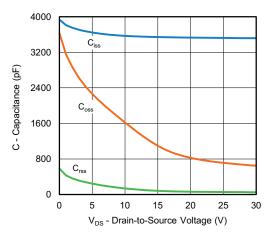


On-Resistance vs. Drain Current and Gate Voltage

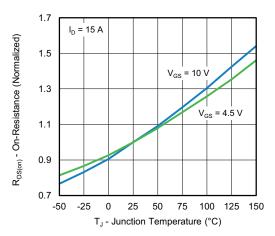




Transfer Characteristics

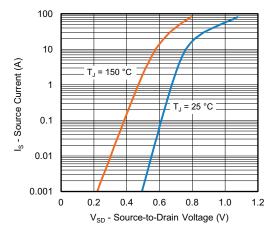


Capacitance

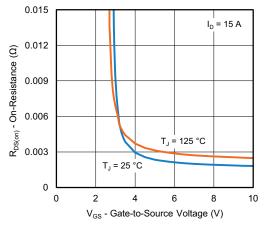


On-Resistance vs. Junction Temperature

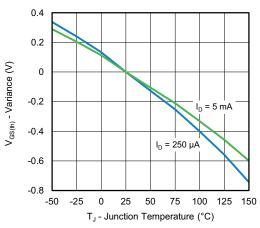




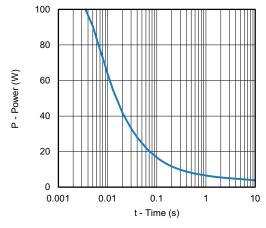
Source-Drain Diode Forward Voltage



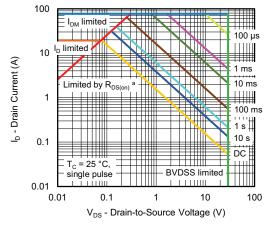
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



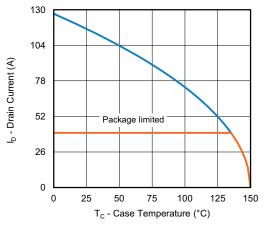
Single Pulse Power, Junction-to-Ambient



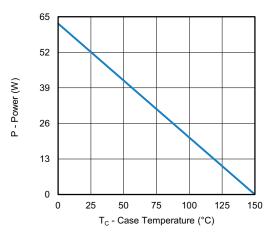
Safe Operating Area, Junction-to-Ambient

Note

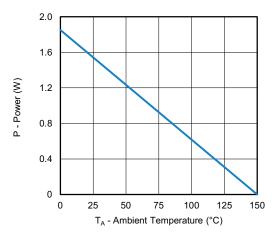
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Current Derating a





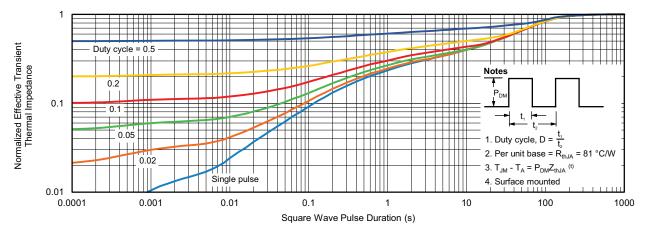


Power, Junction-to-Ambient

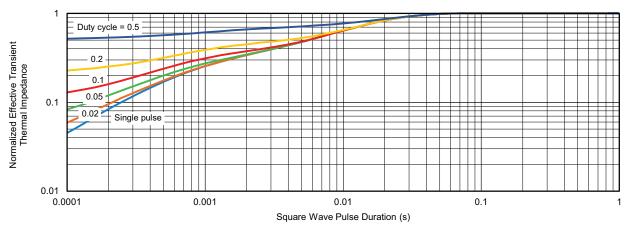
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

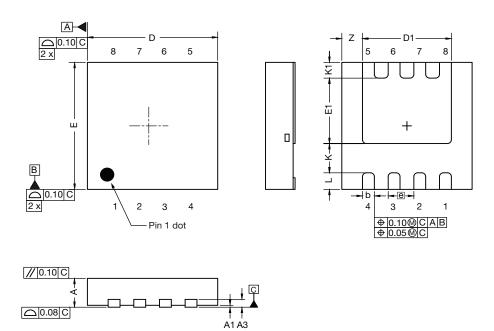
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Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH



DIM.	MILLIMETERS			INCHES			
DIIVI.	MIN.	NOM.	MAX.	X. MIN. NOM.	NOM.	MAX.	
Α	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е	0.65 bsc.			0.026 bsc.			
K		0.76 ref.		0.76 ref. 0.030 ref.			
K1	0.41 ref.		0.016 ref.				
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.		0.021 ref.				

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